Date	User	Film	Recipe	Substrate T	Thickness	Dep.time	JAW EC-400 (Woolam Spectroscopic		Dep.rate	Stress	HF etch rate wafer	AVG dep.rate	AVG+10%	AVG-10%	AVG index@632	AVG+2%	AVG-2%	Additional Notes
					Wafer center													
1/1/2012	User	SiN	SiN_10	250 °C	(Å)	sec	index @ 632.8nm	index @ 1550nm	(nm/min)	Mpa	(nm/min)							
01/06/14	Biljana	SiN	SiN_10	250	1055.25	568.1	1.949	1.899	11.15	571.87		11.21	12.33	10.09	1.959	1.998	1.920	4" Si wafer
01/23/14	Biljana	SiN	SiN_10	250	1133.40	568.1	1.935	1.890	11.97	446.88	90.66	11.21	12.33	10.09	1.959	1.998	1.920	4" Si wafer
02/03/14	Biljana	SiN	SiN_10	250	1046.60	568.1	1.937	1.893	11.05	486.75	81.21	11.21	12.33	10.09	1.959	1.998	1.920	4" Si wafer
02/19/14	Biljana	SiN	SiN_10	250	1030.66	568.1	1.935	1.890	10.89	353.92	77.32	11.21	12.33	10.09	1.959	1.998	1.920	4" Si wafer
03/14/14	Biljana	SiN	SiN_10	250	1042.16	568.1	1.933	1.887	11.01	684.87	92.89	11.21	12.33	10.09	1.959	1.998	1.920	4" Si wafer

Avg.Thickness 1061.614

Avg. Stress 508.858

Avg. HF etch rate 85.520

Avg. Index 1.938 Avg Dep.Rate 11.21

Avg+2% 1.977 Avg +10% 12.33

Avg-2% 1.899 Avg - 10% 10.09